

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Cyril Cabral, Jr., et al.

Examiner: Unassigned

Serial No: Unassigned

Art Unit: Unassigned

Filed: Herewith

Docket: YOR919990509US2 (13171A)

For: METHOD AND STRUCTURE FOR
REDUCTION OF CONTACT RESISTANCE
OF METAL SILICIDES USING A METAL-
GERMANIUM ALLOY

Dated: November 27, 2001

Assistant Commissioner for Patents
United States Patent and Trademark Office
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

In connection with filing the above-identified patent application under 37 C.F.R. §1.53(b), applicants submit the following amendments and remarks for entry of record in the above-identified patent application.

CERTIFICATE OF MAILING BY EXPRESS MAIL

Express Mail Mailing Label Number: **EV 052766279 US**
Date of Deposit: **November 27, 2001**

I hereby certify that this correspondence is being deposited with the United States Postal Service Express Mail Post Office to Addressee service under 37 C.F.R. §1.10 on the date indicated above and is addressed to the Assistant Commissioner of Patents and Trademarks, Washington, D.C. 20231.

Dated: November 27, 2001

Janet Grossman
Janet Grossman

IN THE SPECIFICATION:

Page 1, after the heading “DESCRIPTION” please insert the following:

--RELATED APPLICATIONS

This application is a divisional application of U.S. application Serial No. 09/519,897, filed on March 6, 2000.--

IN THE CLAIMS:

Please cancel Claims 1-22, without prejudice or disclaimer, and add the following new claims:

- 25. The electrical contact of Claim 23 wherein said silicon-containing semiconductor material comprises single crystal Si, polycrystalline Si, SiGe, amorphous Si or a silicon-on-insulator (SOI).
26. The electrical contact of Claim 23 wherein said metal of said disilicide is Co and said metal silicide is Co disilicide.
27. The electrical contact of Claim 23 wherein said metal of said disilicide is Ti and said metal silicide is TiSi₂.
28. The electrical contact of Claim 27 wherein said TiSi₂ is in the C54 phase.
29. The electrical contact of Claim 23 further comprising an oxide layer present near a surface of said substrate.
30. The electrical contact of Claim 29 wherein said oxide layer has a thickness of from about 0.1 to about 3.0 nm.
31. The electrical contact of Claim 23 wherein said substrate is doped.

32. The electrical contact of Claim 24 wherein said silicon-containing semiconductor material comprises single crystal Si, polycrystalline Si, SiGe, amorphous Si or a silicon-on-insulator (SOI).

33. The electrical contact of Claim 24 further comprising an oxide layer present near a surface of said substrate.

34. The electrical contact of Claim 33 wherein said oxide layer has a thickness of from about 0.1 to about 3.0 nm.

35. The electrical contact of Claim 24 wherein said substrate is doped.--

REMARKS

Favorable consideration and allowance of the claims of the present application, as presently filed, are respectfully requested.

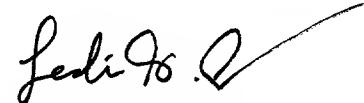
In this preliminary amendment, applicants have canceled original Claims 1-22 herein since those claims are the subject matter of parent application U.S. Serial No. 09/519,897 filed March 6, 2000 and have amended the specification to include information regarding the parent application.

Additionally, applicants have added new claims 25-35 which are directed to specific embodiments of the present invention. Support for the newly added claims is found throughout the specification of the instant application. For example, support for new Claims 25 and 32 is found at Page 7, lines 27-30; support for new Claims 26-28 is found at Page 5, line 29-Page 6, line 4; support for new Claims 29, 30, 33 and 34 is found at Page 7, lines 22-26 and lines 31-32; and support for new Claims 31 and 35 is found at Page 8, line 8.

Since the above amendments to the specification and claims do not introduce any new matter into the application, entry thereof is respectfully requested.

Wherefore, consideration and allowance of the claims of the present application are respectfully requested.

Respectfully submitted,



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